

## ABSTRACT

The ion implanting method uses both reciprocatively scanning an ion beam in an X direction and reciprocatively mechanically driving a substrate in a Y direction  
5 orthogonal thereto. An implanting step of implanting ions separately for two implanted regions with different dose amounts of the substrate is executed plural times by changing at the center of the substrate a driving speed  
10 of the substrate. A rotating step of rotating the substrate around its center by a prescribed angle is executed once during each of the intervals between the respective implanting steps and while the ion beam is not applied to the substrate.